



## N-Channel 30-V (D-S) MOSFET

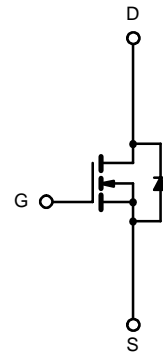
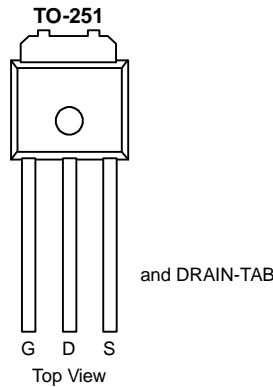
PRODUCT SUMMARY		
$V_{DS}$ (V)	$r_{DS(on)}$ ( $\Omega$ )	$I_D$ (A) <sup>b</sup>
30	0.0095 @ $V_{GS} = 10$ V	63 <sup>b</sup>
	0.014 @ $V_{GS} = 4.5$ V	52 <sup>b</sup>

### FEATURES

- TrenchFET® Power MOSFET
- Optimized for High- or Low-Side

### APPLICATIONS

- DC/DC Converters
- Synchronous Rectifiers



Order Number: SUU50N03-09P  
SUU50N03-09P—E3 (Lead (Pb)-Free)

N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)				
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		$V_{DS}$	30	V
Gate-Source Voltage		$V_{GS}$	$\pm 20$	
Continuous Drain Current <sup>a</sup>	$T_C = 25^\circ\text{C}$	$I_D$	63 <sup>b</sup>	A
	$T_C = 100^\circ\text{C}$		44.5 <sup>b</sup>	
Pulsed Drain Current		$I_{DM}$	50	
Continuous Source Current (Diode Conduction) <sup>a</sup>		$I_S$	10	
Avalanche Current	L = 0.1 mH	$I_{AS}$	35	
Single Pulse Avalanche Energy		$E_{AS}$	61	mJ
Maximum Power Dissipation	$T_C = 25^\circ\text{C}$	$P_D$	65.2	W
	$T_A = 25^\circ\text{C}$		7.5 <sup>a</sup>	
Operating Junction and Storage Temperature Range		$T_J, T_{stg}$	-55 to 175	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>a</sup>	$t \leq 10$ sec	$R_{thJA}$	16	20	$^\circ\text{C/W}$
	Steady State		40	50	
Maximum Junction-to-Case		$R_{thJC}$	1.8	2.3	

Notes

- a. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
- b. Based on maximum allowable Junction Temperature, package limitation current is 50 A.

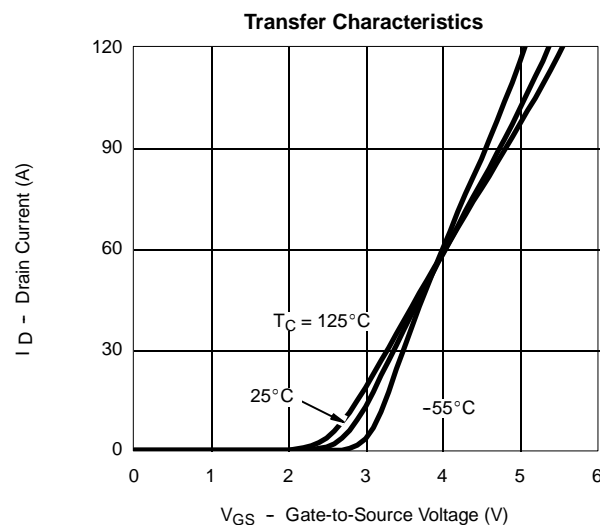
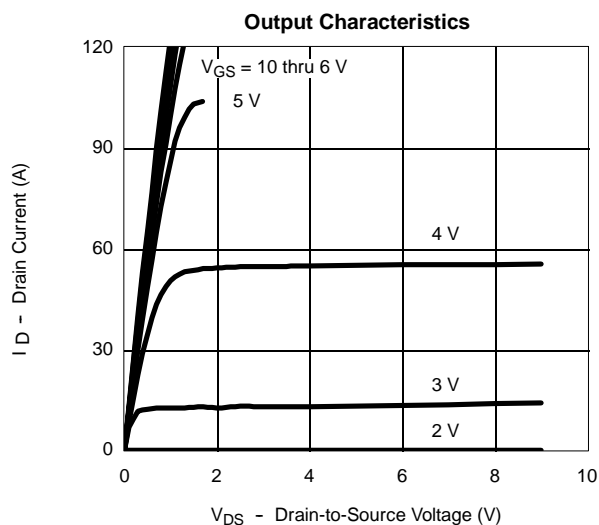


SPECIFICATIONS (T <sub>J</sub> = 25°C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Condition	Min	Typ <sup>a</sup>	Max	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	30			V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	1.0		3.0	
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V			1	μA
		V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125°C			50	
On-State Drain Current <sup>b</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = 5 V, V <sub>GS</sub> = 10 V	50			A
Drain-Source On-State Resistance <sup>b</sup>	r <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A		0.0076	0.0095	Ω
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A, T <sub>J</sub> = 125°C			0.015	
		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 20 A		0.0115	0.014	
Forward Transconductance <sup>b</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 20 A	20			S
<b>Dynamic<sup>a</sup></b>						
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 25 V, f = 1 MHz		2200		pF
Output Capacitance	C <sub>oss</sub>			410		
Reverse Transfer Capacitance	C <sub>rss</sub>			180		
Gate Resistance	R <sub>g</sub>			1.5		Ω
Total Gate Charge <sup>c</sup>	Q <sub>g</sub>	V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 50 A		15	23	nC
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>			7.5		
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			5.0		
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>	V <sub>DD</sub> = 15 V, R <sub>L</sub> = 0.3 Ω I <sub>D</sub> ≅ 50 A, V <sub>GEN</sub> = 10 V, R <sub>g</sub> = 2.5 Ω		9	15	ns
Rise Time <sup>c</sup>	t <sub>r</sub>			80	120	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			22	35	
Fall Time <sup>c</sup>	t <sub>f</sub>			8	12	
<b>Source-Drain Diode Ratings and Characteristic (T<sub>C</sub> = 25°C)</b>						
Pulsed Current	I <sub>SM</sub>				100	A
Diode Forward Voltage <sup>b</sup>	V <sub>SD</sub>	I <sub>F</sub> = 50 A, V <sub>GS</sub> = 0 V		1.2	1.5	V
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 50 A, di/dt = 100 A/μs		35	70	ns

### Notes

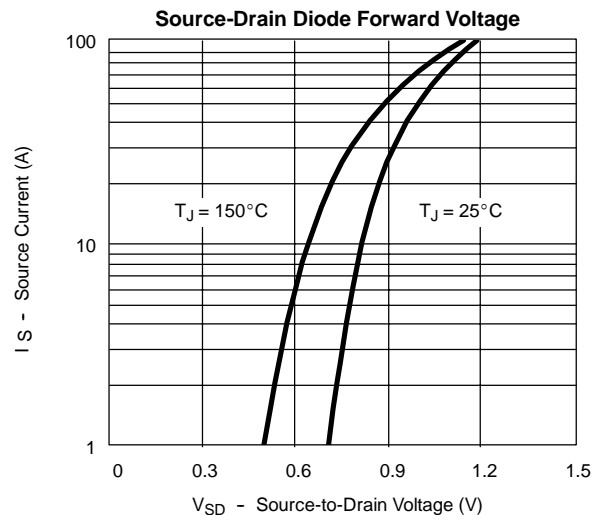
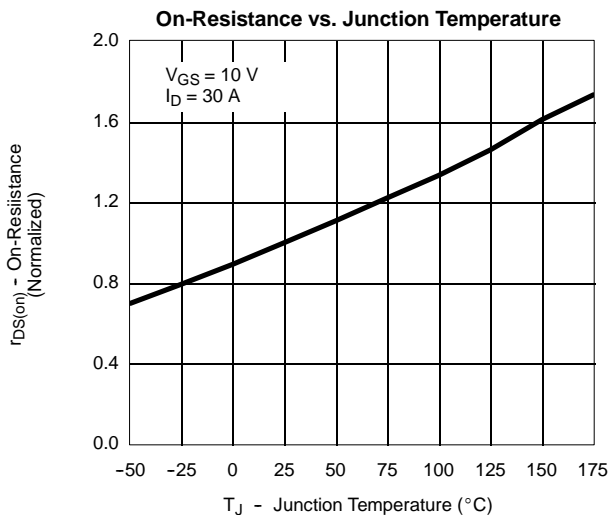
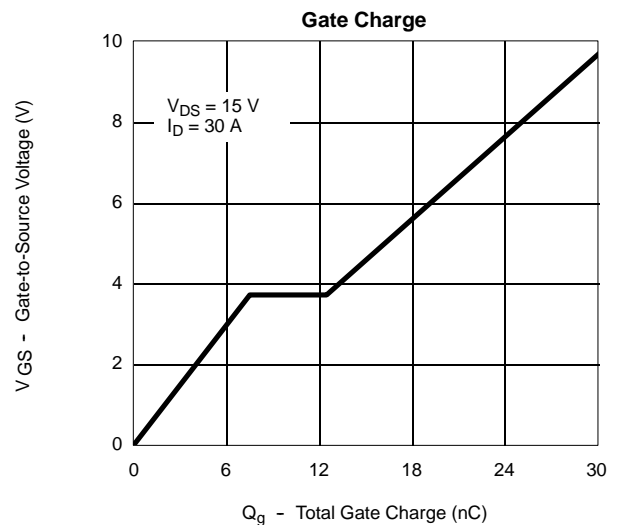
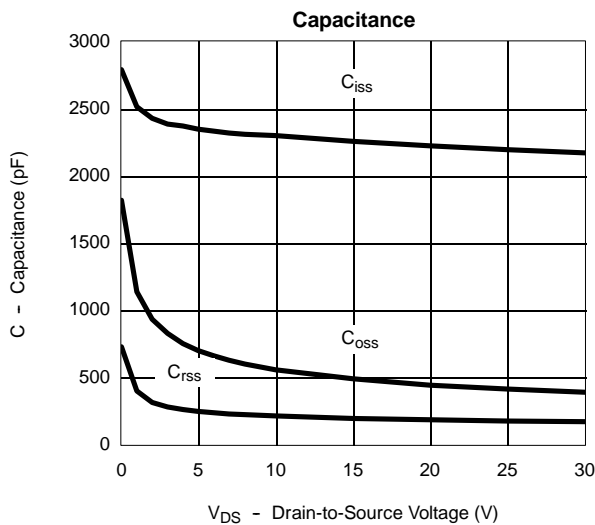
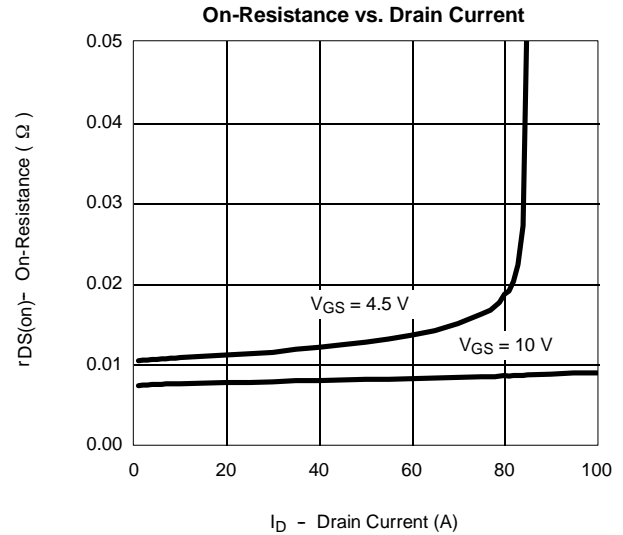
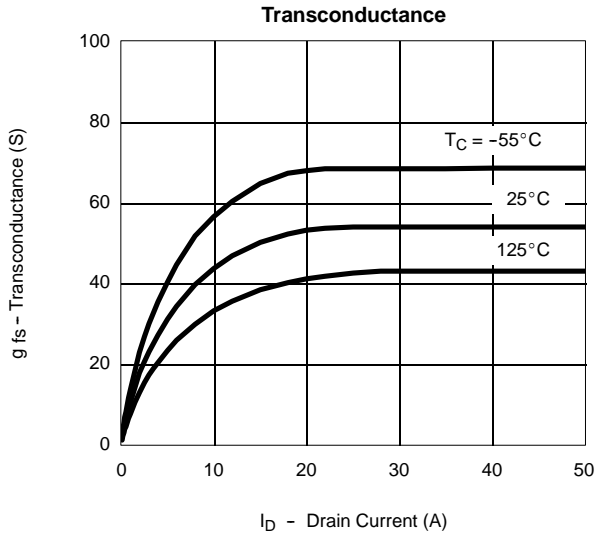
- Guaranteed by design, not subject to production testing.
- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
- Independent of operating temperature.

## TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)



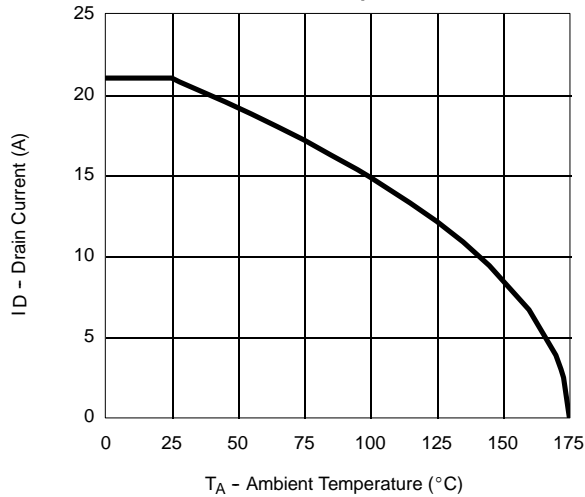


**TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)**

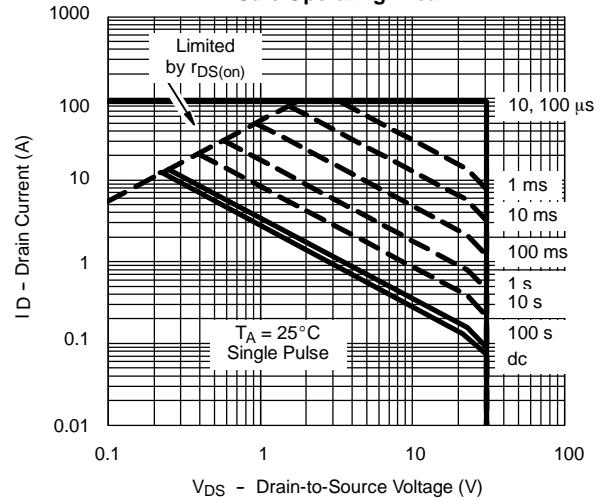


**THERMAL RATINGS**

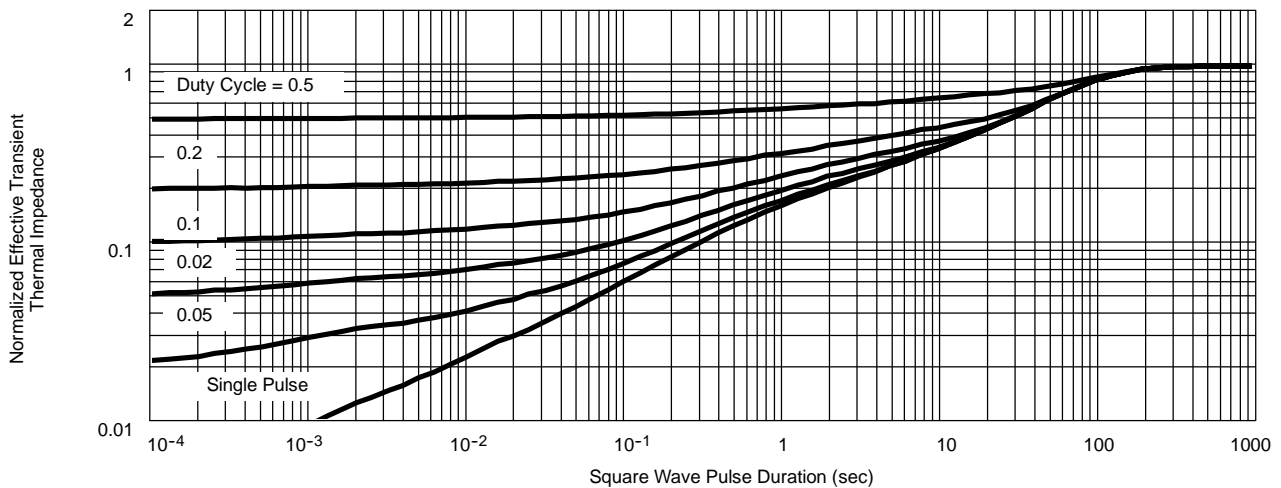
Maximum Drain Current vs. Ambient Temperature



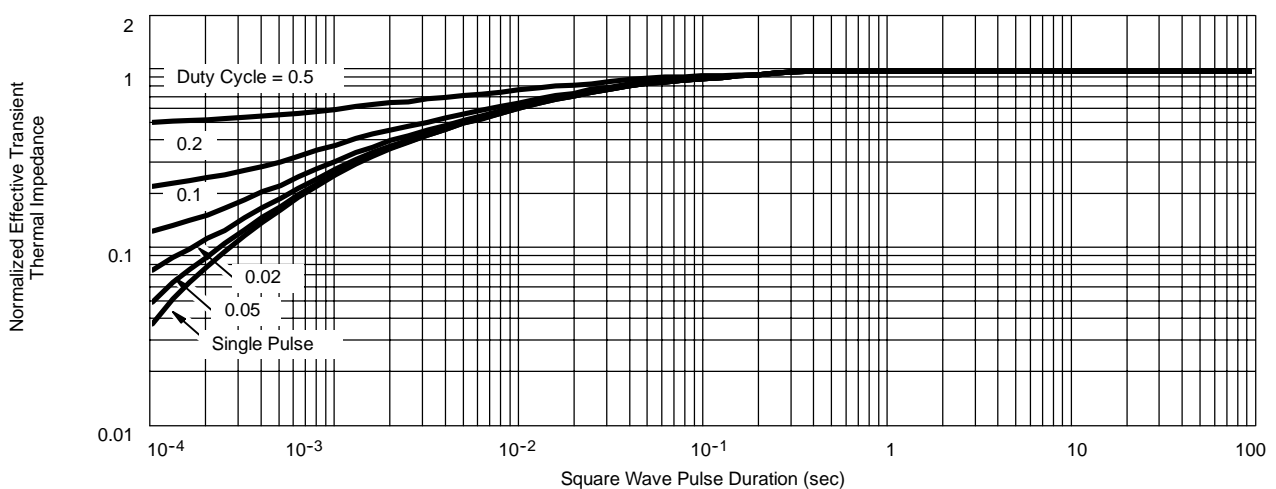
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case





## Disclaimer

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